

FEATURES

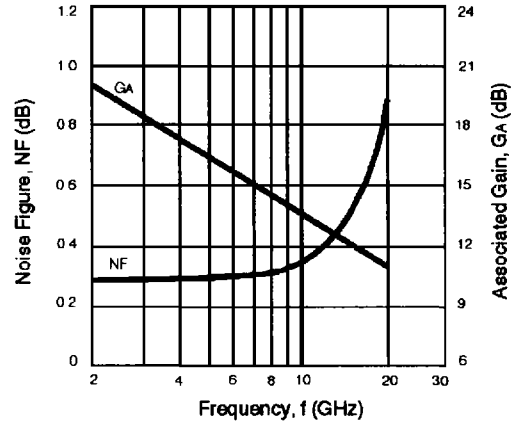
- **VERY LOW NOISE FIGURE:**
0.40 dB Typical at 12 GHz
- **HIGH ASSOCIATED GAIN:**
12.5 dB Typical at 12 GHz
- **LG ≤ 0.20 μm, WG = 200 μm**
- **LOW COST METAL CERAMIC PACKAGE**
- **TAPE & REEL PACKAGING OPTION AVAILABLE**

DESCRIPTION

The NE32984D is a pseudomorphic Hetero-Junction FET that uses the junction between Si-doped AlGaAs and undoped InGaAs to create very high mobility electrons. The device features mushroom shaped TiAl gates for decreased gate resistance and improved power handling capabilities. The mushroom gate also results in lower noise figure and high associated gain. This device is housed in an epoxy-sealed, metal/ceramic package and is intended for high volume consumer and industrial applications.

NEC's stringent quality assurance and test procedures assure the highest reliability and performance.

**NOISE FIGURE & ASSOCIATED
GAIN vs. FREQUENCY**
V_{DS} = 2 V, I_{DS} = 10 mA



ELECTRICAL CHARACTERISTICS (T_A = 25°C)

PART NUMBER PACKAGE OUTLINE			NE32984D 84D		
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
NF ¹	Optimum Noise Figure, V _{DS} = 2 V, I _{DS} = 10 mA, f = 12 GHz	dB		0.40	0.50
GA ¹	Associated Gain, V _{DS} = 2 V, I _{DS} = 10 mA, f = 12 GHz	dB	11.0	12.5	
I _{DSS}	Saturated Drain Current, V _{DS} = 2 V, V _{GS} = 0 V	mA	20	60	90
V _P	Pinch-off Voltage, V _{DS} = 2 V, I _{DS} = 100 μA	V	-2.0	-0.7	-0.2
g _m	Transconductance, V _{DS} = 2 V, I _D = 10 mA	mS	45	60	
I _{GSO}	Gate to Source Leakage Current, V _{GS} = -3 V	μA		0.5	10.0
R _{TH(CH-A)}	Thermal Resistance (Channel to Ambient)	°C/W		750	
R _{TH(CH-C)}	Thermal Resistance (Channel to Case)	°C/W			350

Note:

1. Typical values of noise figures and associated gain are those obtained when 50% of the devices from a large number of lots were individually measured in a circuit with the input individually tuned to obtain the minimum value. Maximum values are criteria established on the production line as a "go-no-go" screening tuned for the "generic" type but not each specimen.

CAEL5017

ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{DS}	Drain to Source Voltage	V	4.0
V _{GS}	Gate to Source Voltage	V	-3.0
I _{DS}	Drain Current	mA	I _{DSS}
I _{GRF}	Gate Current	μA	100
T _{CH}	Channel Temperature	°C	150
T _{STG}	Storage Temperature	°C	-65 to +150
P _T	Total Power Dissipation	mW	165

Note:

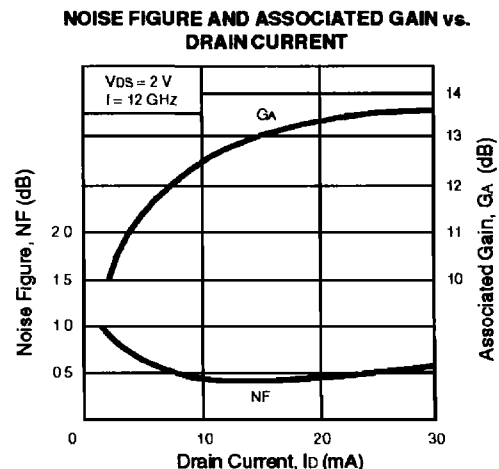
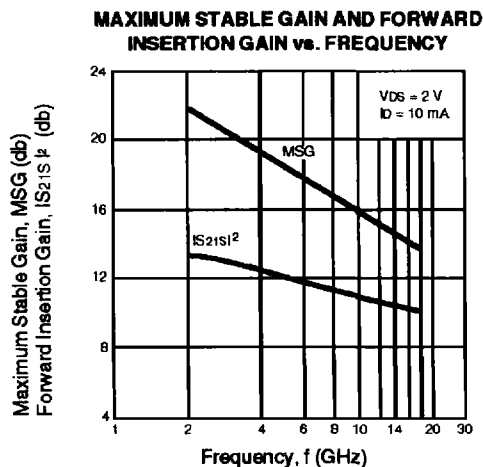
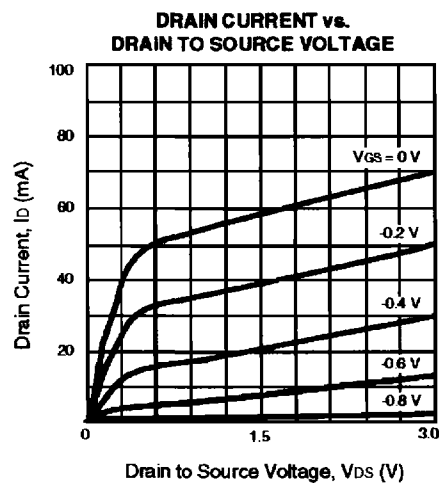
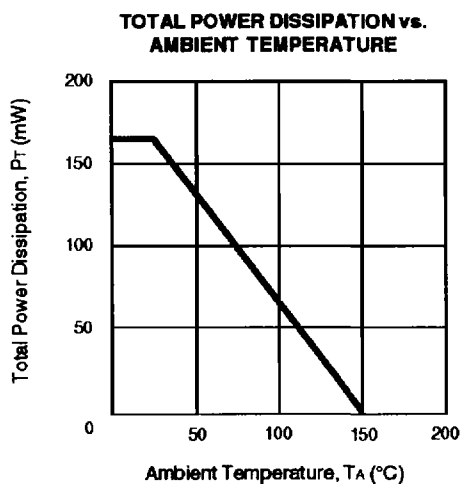
1. Operation in excess of any one of these parameters may result in permanent damage.

NOISE PARAMETERS

V_{DS} = 2 V, I_D = 10 mA

FREQ. (GHz)	NF _{MIN.} (dB)	GA (dB)	Γ _{opt}		R _n /50
			MAG	ANG	
2.0	0.29	20.0	0.85	20	0.30
4.0	0.30	18.3	0.75	41	0.28
6.0	0.31	16.5	0.68	63	0.20
8.0	0.34	15.0	0.61	86	0.13
10.0	0.37	13.6	0.56	111	0.09
12.0	0.40	12.5	0.52	137	0.05
14.0	0.49	12.0	0.47	164	0.04
16.0	0.63	11.8	0.40	-168	0.04
18.0	0.81	11.5	0.31	-139	0.07

TYPICAL PERFORMANCE CURVES (T_A = 25°C)



TYPICAL SCATTERING PARAMETERS (T_A = 25°C)

NE32984D

V_{DS} = 2 V, I_D = 10 mA

FREQUENCY (GHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K	MAG ¹ (dB)
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		
2	.984	-26.4	4.583	146.9	.029	66.4	.549	-32.0	.13	22.0
3	.960	-39.3	4.480	130.6	.041	55.9	.520	-47.8	.22	20.4
4	.919	-52.8	4.332	114.3	.050	47.9	.481	-64.5	.31	19.4
5	.868	-64.5	4.141	98.8	.057	38.5	.447	-81.9	.45	18.6
6	.816	-75.5	3.923	84.4	.060	31.2	.418	-99.8	.58	18.2
7	.786	-85.7	3.786	70.8	.064	26.0	.396	-116.7	.63	17.7
8	.759	-95.9	3.659	57.1	.068	21.7	.382	-132.6	.69	17.4
9	.736	-106.3	3.547	43.1	.068	18.2	.374	-147.8	.75	17.2
10	.689	-116.2	3.375	30.1	.071	16.0	.368	-163.0	.86	16.8
11	.659	-125.6	3.264	17.5	.074	13.2	.370	-178.3	.91	16.4
12	.621	-135.5	3.217	4.9	.079	11.4	.374	-167.4	.94	16.1
13	.590	-146.3	3.186	-8.0	.085	7.3	.391	-155.0	.92	15.7
14	.554	-157.9	3.172	-21.3	.093	2.0	.406	-143.2	.91	15.3
15	.522	-171.0	3.180	-35.2	.104	-5.5	.417	-132.1	.86	14.9
16	.491	-173.0	3.220	-49.9	.114	-12.6	.432	-119.7	.82	14.5
17	.461	-153.2	3.303	-65.6	.124	-23.3	.445	-106.3	.78	14.3
18	.452	-129.4	3.367	-83.4	.137	-36.4	.453	-91.0	.72	13.9

Note:

1. Gain calculation:

$$\text{MAG} = \frac{|S_{21}|}{|S_{12}|} (K \pm \sqrt{K^2 - 1}). \text{ When } K \leq 1, \text{ MAG is undefined and MSG values are used. } \text{MSG} = \frac{|S_{21}|}{|S_{12}|}, K = \frac{1 + |\Delta|^2 - |S_{11}|^2 - |S_{22}|^2}{2 |S_{12}| |S_{21}|}, \Delta = S_{11} S_{22} - S_{21} S_{12}$$

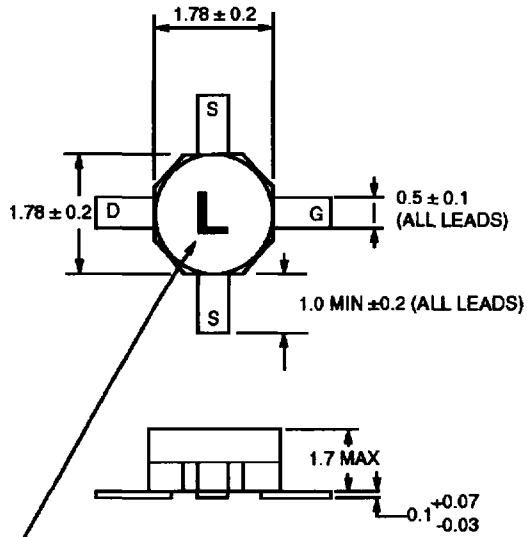
MAG = Maximum Available Gain

MSG = Maximum Stable Gain

NE32984D

OUTLINE DIMENSIONS (Units in mm)

PACKAGE OUTLINE 84D



Part Number Designator (Letter).
When the letter is upright,
the gate lead is to the right.

ORDERING INFORMATION

PART NUMBER	AVAILABILITY	LEAD LENGTH	PACKAGE OUTLINE
NE32984D-S	Bulk up to 1K	1.0 mm	84D
NE32984D-T1	1K/Reel	1.0 mm	84D
NE32984D-SL	Bulk up to 1K	1.7 mm	84D-SL

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